

0.3 ~ 1.0GHz GaN 10W High Power Solid State Power Amplifier Module

FEATURES

- Freq : 0.3 ~ 1.0 GHz Full Band
- Pin : 0 ~ +5dBm
- Psat : 40dBm, min.

ELECTRICAL SPECIFICATIONS (@+24V VDC, 25°C)

Parameter	Min	Typ	Max	Unit	Remark
Operating Frequency	300		1000	MHz	
Power Output, Psat	40.0	40.5		dBm	@0dBm Pin
Input Power	0		+5	dBm	
Small Signal Gain		48		dB	
Input VSWR			2.0:1		
Output VSWR		2.0:1	2.5:1		
Non-harmonic Spurious		-50		dBc	
Operating DC Voltage	+23	+24	+25	Volt	
Efficiency	40			%	@Psat

NOTE - .

Mechanical Specification

Parameter	Value	Units
Dimensions	78 x 58 x 12, typ., as shown on page 2	mm
RF Connectors In/Out	Input: SMA Female ; Output: SMA Female	
DC & Control Connectors	Feedthrough soldered pins	
Cooling	External Heatsink is required (by customer)	

ENVIRONMENTAL CHARACTERISTICS

Parameter	Min	Typ	Max	Unit	Remark
Operating Temperature***	-40		+75	°C	Baseplate(Case)
Storage Temperature	-40		+85	°C	
Relative humidity (non-condensing)			95	%	
Cooling	External heatsink is required by the customer				

NOTE - ***For the better MTBF of long-time operation, Transcom strongly suggest the customer's system to equip with sufficient heatsink for keeping the amplifier baseplate(case) temp below the maximum specs temp(+65C)

RF ON / OFF, PROTECTIONS, MONITORING

Parameter	Value	Remark
RF On/ Off	Enable: TTL 1(High), Disable: TTL 0(Low)	
RF Off Current	50mA, max	TTL Low
Current Monitoring	Vdet / 3	Unit: amper
Input Power	+12dBm, max.	Without damage

MECHANICAL DRAWING, unit: mm

